# TIP29, A, B, C (NPN), **TIP30, A, B, C (PNP)**

# **Complementary Silicon Plastic Power Transistors**

Designed for use in general purpose amplifier and switching applications. Compact TO-220 package.

#### **Features**

• These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage TIP29G, TIP30G TIP29AG, TIP30AG TIP29BG, TIP30BG TIP29CG, TIP30CG	V <sub>CEO</sub>	40 60 80 100	Vdc
Collector - Base Voltage TIP29G, TIP30G TIP29AG, TIP30AG TIP29BG, TIP30BG TIP29CG, TIP30CG	V <sub>CB</sub>	40 60 80 100	Vdc
Emitter – Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	1.0	Adc
Collector Current - Peak	I <sub>CM</sub>	3.0	Adc
Base Current	Ι <sub>Β</sub>	0.4	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	30 0.24	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. This rating based on testing with  $L_C = 20$  mH,  $R_{BE} = 100 \Omega$ ,  $V_{CC} = 10 V$ ,  $I_C = 1.8 \text{ A}, P.R.F = 10 \text{ Hz}$ 

#### THERMAL CHARACTERISTICS

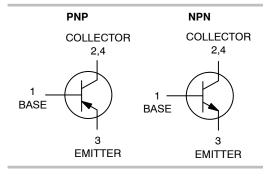
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.167	°C/W



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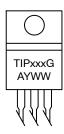
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## 1 AMPERE **POWER TRANSISTORS COMPLEMENTARY SILICON** 40, 60, 80, 100 VOLTS, **80 WATTS**





#### **MARKING DIAGRAM**



TIPxxx = Device Code:

29, 29A, 29B, 29C 30, 30A, 30B, 30C

= Assembly Location

= Year ww = Work Week = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 4 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## TIP29, A, B, C (NPN), TIP30, A, B, C (PNP)

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>'</u>			U.
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0) (Note 2) TIP29G, TIP30G TIP29AG, TIP30AG TIP29BG, TIP30BG TIP29CG, TIP30CG	V <sub>CEO(sus)</sub>	40 60 80 100	- - - -	Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ TIP29G, TIP29AG, TIP30G, TIP30AG $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ TIP29BG, TIP29CG, TIP30BG, TIP30CG	ICEO	-	0.3 0.3	mAdc
Collector Cutoff Current $ (V_{CE} = 40 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP29G}, \text{TIP30G} $ $ (V_{CE} = 60 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP29AG}, \text{TIP30AG} $ $ (V_{CE} = 80 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP29BG}, \text{TIP30BG} $ $ (V_{CE} = 100 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP29CG}, \text{TIP30CG} $	I <sub>CES</sub>	-	200 200 200 200	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	1.0	mAdc
ON CHARACTERISTICS (Note 2)	<b>'</b>		l	-I
DC Current Gain ( $I_C = 0.2$ Adc, $V_{CE} = 4.0$ Vdc) ( $I_C = 1.0$ Adc, $V_{CE} = 4.0$ Vdc)	h <sub>FE</sub>	40 15	_ 75	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 1.0 Adc, I <sub>B</sub> = 125 mAdc)	V <sub>CE(sat)</sub>	-	0.7	Vdc
Base–Emitter On Voltage ( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	-	1.3	Vdc
DYNAMIC CHARACTERISTICS	<del>.</del>			•
Current-Gain - Bandwidth Product (Note 3) (I <sub>C</sub> = 200 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f⊤	3.0	-	MHz
Small–Signal Current Gain ( $I_C = 0.2$ Adc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz)	h <sub>fe</sub>	20	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0% 3.  $f_T = |h_{fe}| \bullet f_{test}$ 

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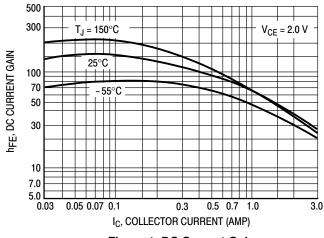


Figure 1. DC Current Gain

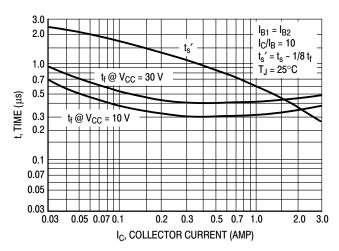


Figure 2. Turn-Off Time

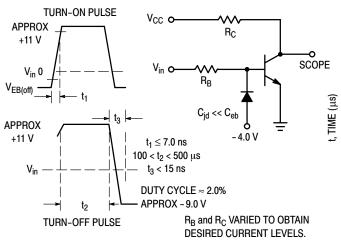


Figure 3. Switching Time Equivalent Circuit

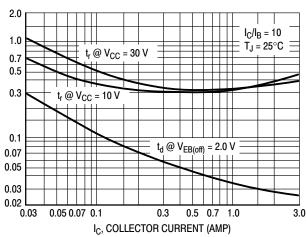


Figure 4. Turn-On Time

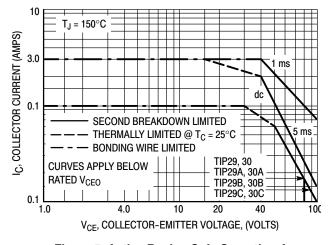


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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## **ORDERING INFORMATION**

Device	Package	Shipping
TIP29G	TO-220 (Pb-Free)	50 Units / Rail
TIP29AG	TO-220 (Pb-Free)	50 Units / Rail
TIP29BG	TO-220 (Pb-Free)	50 Units / Rail
TIP29CG	TO-220 (Pb-Free)	50 Units / Rail
TIP30G	TO-220 (Pb-Free)	50 Units / Rail
TIP30AG	TO-220 (Pb-Free)	50 Units / Rail
TIP30BG	TO-220 (Pb-Free)	50 Units / Rail
TIP30CG	TO-220 (Pb-Free)	50 Units / Rail

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